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PATENT NUMBER
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10099963	FILING DATE 03/19/2002	CLASS 438	SUBCLASS 149	GAU 2823	EXAMINER <i>Long Pham</i>
**APPLICANTS: Miyasaka Mitsutoshi;					
**CONTINUING DATA VERIFIED: THIS APPLICATION IS A DIV OF 09/400,303 09/21/1999 WHICH IS A DIV OF 08/776,545 01/31/1997 PAT 6,066,516 <i>Long Pham</i>					
**FOREIGN APPLICATIONS VERIFIED: JAPAN 7-159147 06/26/1995 JAPAN 8-161280 06/21/1996					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners's initials				ATTORNEY DOCKET NO. 038839.02	
TITLE: Method for forming crystalline semiconductor layers, a method for fabricating thin film transistors, and a method for fabricating solar cells and active matrix liquid crystal devices U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)					

NOTICE OF ALLOWANCE MAILED		CLAIMS	
		Total Claims	0.0
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheet/Draw	Page/fig
<input type="checkbox"/> TERMINAL DISCLAIMER		Application Examiner	
		PREPARED FOR ISSUE	
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